

MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK8A60W



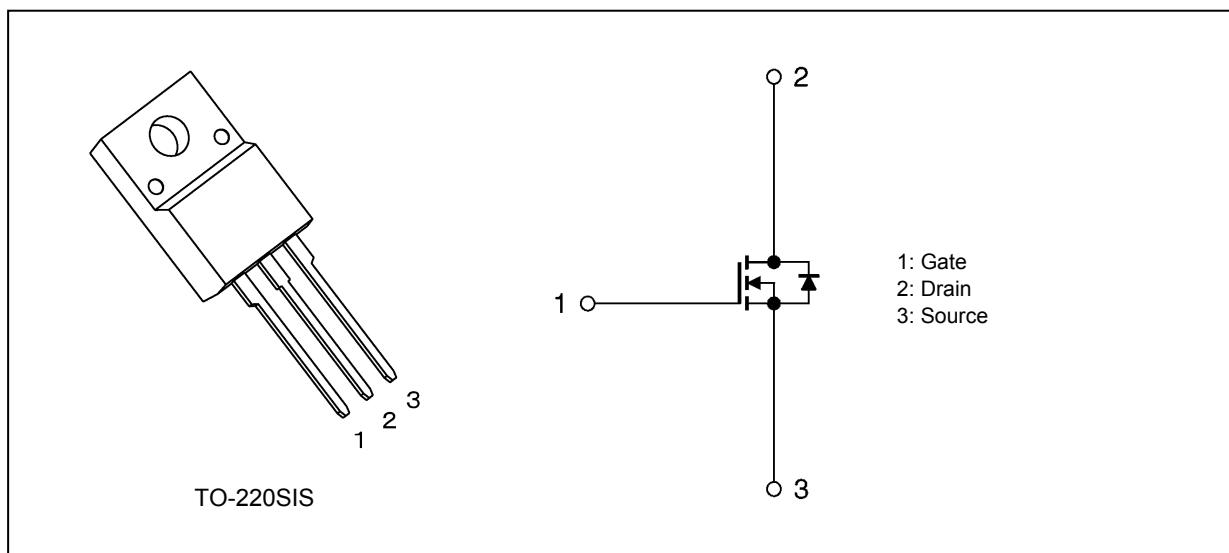
1. Applications

- Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.42 \Omega$ (typ.)
by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: $V_{th} = 2.7$ to 3.7 V ($V_{DS} = 10$ V, $I_D = 0.4$ mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	600	V
Gate-source voltage	V_{GSS}	± 30	
Drain current (DC)	I_D	8.0	A
Drain current (pulsed)	I_{DP}	32	
Power dissipation ($T_c = 25^\circ\text{C}$)	P_D	30	W
Single-pulse avalanche energy	E_{AS}	105	mJ
Avalanche current	I_{AR}	2.0	A
Reverse drain current (DC)	I_{DR}	8.0	
Reverse drain current (pulsed)	I_{DRP}	32	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to 150	
Isolation voltage (RMS) ($t = 1.0$ s)	$V_{ISO(RMS)}$	2000	V
Mounting torque	T_{OR}	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 1	μA
Drain cut-off current	I_{DSS}	$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	600	—	—	
Gate threshold voltage	V_{th}	$V_{DS} = 10 \text{ V}, I_D = 0.4 \text{ mA}$	2.7	—	3.7	
Drain-source on-resistance	$R_{DS(\text{ON})}$	$V_{GS} = 10 \text{ V}, I_D = 4.0 \text{ A}$	—	0.42	0.5	Ω

6.2. Dynamic Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	$V_{DS} = 300 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	570	—	pF
Reverse transfer capacitance	C_{rss}		—	2.5	—	
Output capacitance	C_{oss}		—	16	—	
Effective output capacitance	$C_{o(er)}$	$V_{DS} = 0 \text{ to } 400 \text{ V}, V_{GS} = 0 \text{ V}$	—	26	—	
Gate resistance	r_g	$V_{DS} = \text{OPEN}, f = 1 \text{ MHz}$	—	7.5	—	Ω
Switching time (rise time)	t_r	See Figure 6.2.1	—	20	—	ns
Switching time (turn-on time)	t_{on}		—	40	—	
Switching time (fall time)	t_f		—	5.5	—	
Switching time (turn-off time)	t_{off}		—	70	—	
MOSFET dv/dt ruggedness	dv/dt	$V_{DD} = 0 \text{ to } 400 \text{ V}, I_D = 4.0 \text{ A}$	50	—	—	V/ns

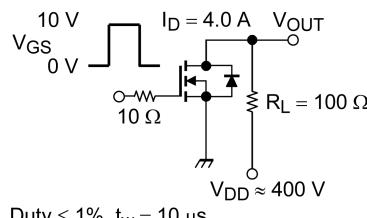


Fig. 6.2.1 Switching Time Test Circuit

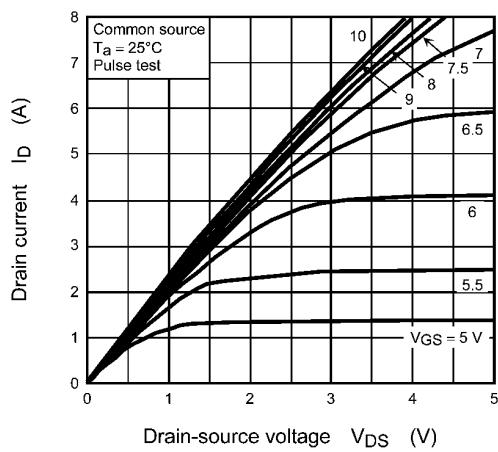
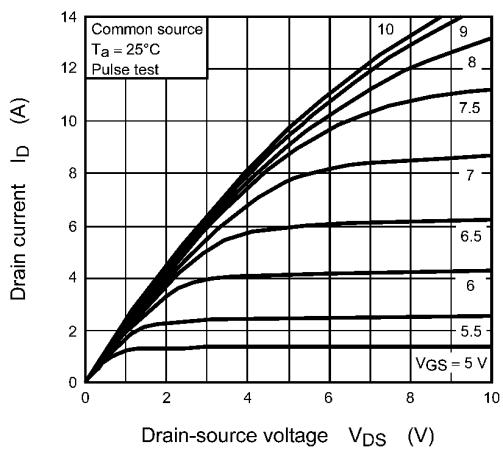
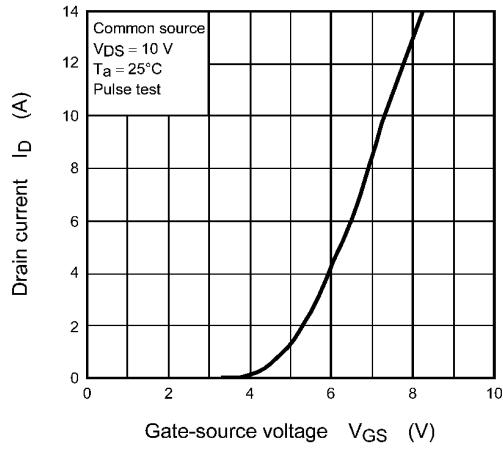
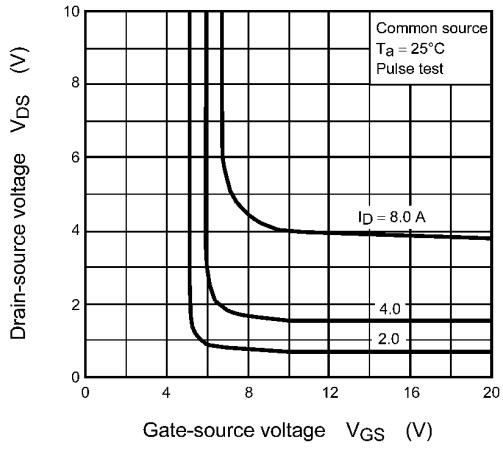
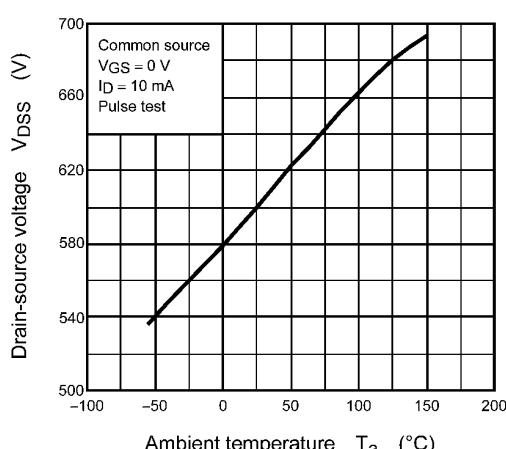
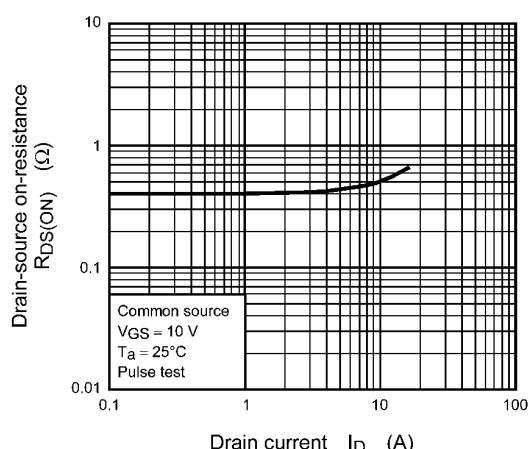
6.3. Gate Charge Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8.0 \text{ A}$	—	18.5	—	nC
Gate-source charge 1	Q_{gs1}		—	3.5	—	
Gate-drain charge	Q_{gd}		—	9.0	—	

6.4. Source-Drain Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage	V_{DSF}	$I_{DR} = 8.0 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 4.0 \text{ A}, V_{GS} = 0 \text{ V}$ $-dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	230	—	ns
Reverse recovery charge	Q_{rr}		—	1.9	—	
Peak reverse recovery current	I_{rr}		—	17	—	
Diode dv/dt ruggedness	dv/dt	$I_{DR} = 4.0 \text{ A}, V_{GS} = 0 \text{ V}, V_{DD} = 400 \text{ V}$	15	—	—	V/ns

8. Characteristics Curves (Note)

Fig. 8.1 $I_D - V_{DS}$ Fig. 8.2 $I_D - V_{DS}$ Fig. 8.3 $I_D - V_{GS}$ Fig. 8.4 $V_{DS} - V_{GS}$ Fig. 8.5 $V_{DSS} - T_a$ Fig. 8.6 $R_{DS(ON)} - I_D$